IN THE CLAIMS:

1. (Previously Amended) A method of imaging a pattern onto a substrate provided with a layer of energy-sensitive material, comprising:

performing a first exposure to image partly said pattern;

performing a second exposure to image partly said pattern,

wherein at least one of said first and second exposures is performed using an illumination mode having a substantially dipolar intensity distribution.

2. (Original) A method according to claim 1, wherein the other of said first and second exposures is performed using an illumination mode having an intensity distribution which is substantially one of dipolar, quadrupolar, annular and disk-like.

3. (Previously Amended) A method according to claim 1, wherein a first mask is used to define an image formed by said first exposure and a second mask is used to define an image formed by said second exposure.

4. (Previously Amended) A method according to claim 3, further comprising exchanging masks between said first and second exposures.

5. (Previously Amended) A method according to claim 1, wherein a mask having at least two sub-patterns is used for the first and second exposures, a first of the said sub-patterns being used to define an image formed by the first exposure and the second of the sub-patterns being used to define an image formed by the second exposure.

6. (Previously Amended) A method according to claim 1, wherein said illumination mode is used to image linear features of the pattern oriented substantially perpendicular to an axis joining the respective two poles of said substantially dipolar intensity distribution.

7. (Previously Amended) A method according to claim 6, wherein at least one of a respective mask and a mask sub-pattern is used with said illumination mode exposure and

substantially defines only features of the pattern oriented substantially perpendicularly to the axis joining the respective two poles of said substantially dipolar intensity distribution.

8. (Previously Amended) A method according to claim 1, wherein said illumination mode has an intensity distribution comprising two relatively intense poles and further comprising at least one of: a relatively weak central pole; two relatively weak further poles; and a general relatively weak background intensity.

9. (Previously Amended) A method according to claim 1, further comprising changing at least one of a pole radial position, size and intensity between said first and second exposures.

10. (Previously Amended) A method according to claim 1, wherein said first and second exposures are both performed using dipolar illumination modes and wherein axes of the two dipolar modes are substantially perpendicular to each other.

11. (Previously Amended) A method according to claim 1, wherein at least one of the exposures performed using an illumination mode having a substantially dipolar intensity distribution, is performed using polarized electromagnetic radiation.

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12. (Original) A method according to claim 11, wherein the polarized radiation is linearly polarized.

13. (Previously Amended) A method according to claim 12, wherein the radiation is polarized to have an electric field component oriented substantially perpendicular to an axis joining the respective two poles of the substantially dipole intensity distribution.

14. (Previously Amended) A method according to claim 1, wherein between the first and second exposures, a focus of a pattern on the substrate is adjusted to ensure that both the first and second exposures are performed at a substantially optimum focus.

15. (Previously Amended) A method according to claim 1, wherein at least one of the exposures using an illumination mode having a substantially dipolar intensity distribution is performed using an attenuated phase shift mask.

16. (Previously Amended) A method according to claim 15, wherein an attenuation is chosen to balance an energy of radiation of zeroth- and first-order diffracted beams as they are emerging from said pattern and captured by a projection system used to image the patterns on the substrate.

17. (Previously Amended) A device manufacturing method comprising:

providing a substrate which is at least partially covered by a layer of energy-sensitive material;

providing at least one mask for defining a pattern; and

imaging at least part of said mask pattern onto said substrate using a method according to claim 1.

18 – 22. (Withdrawn)

23. (Previously Added) A method according to claim 3, wherein said first mask is different from said second mask.